

PHASE CONTROL THYRISTORS

Stud Version

Features

- Hermetic ceramic -metal seal
- high dv/dt
- High surge capability
- Tested according to IEC standards
- Types up to 2000V V_{RRM}

Typical Applications

- AC controllers
- Battery charges
- DC motor controls
- Power supplies
- Controlled DC power supplies
- Machine tool controls
- Welding

Major Ratings and Characteristics

Parameters		INRN230S	Units	
I _{T(AV)}		230	А	
	@ T _C	85	°C	
I _{T(RMS)}		360	А	
I _{TSM}	@ 50Hz	5700	А	
	@ 60Hz	5970	А	
l²t	@ 50Hz	163	KA ² s	
	@ 60Hz	149	KA ² s	
V DRM /V RRM		400 to 2000	V	
Тq	typical	150	μѕ	
T J	range	- 40 to 125	°C	



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Toma months	Voltage Code	V _{RRM,} maximum repetitive peak reverse voltage	V _{RSM} , maximum non- repetitive peak reverse voltage	I _{RRM} max. @ T _J = T _J max.	
Type number	Code	V	V	mA	
	04	400	500		
	08	800	900		
	12	1200	1300		
INRN230S	14	1400	1500	15.00	
	16	1600	1700		
	18	1800	1900		
	20	2000	2100		

Forward Conduction

Pa	arameter	INRN230S	Units	Condition	s	
I _{T(AV)}	Maximum average on-state current	230	Α	180° conduction, half sine wave		
	@ Case temperature	85	°C			
I _{T(RMS)}	Maximum RMS on-state current	360	Α	180° conduction, half sine wave @ T _C = 80°C		
I _{TSM} ,	Maximum peak, one-cycle	5700	Α	t = 10ms	No voltage	
	non-repetitive surge current	5970		t = 8.3ms	reapplied	
		4800		t = 10ms	100% V _{RRM}	Sinusoidal
		5000		t = 8.3ms	reapplied	half wave,
l²t	Maximum I 2 t for fusing	163	KA ² s	t = 10ms	No voltage	Initial T _J = T _J
		148		t = 8.3ms	reapplied	max.
		115		t = 10ms	100% V _{RRM}	
		105		t = 8.3ms	reapplied	
$I^2 \checkmark t$	Maximum $I^2 \lor t$ for fusing	1630	KA²√s	t = 0.1 to 10	lms, no voltage rea	pplied
V _{TM}	Maximum on-state or forward	0.92	V	$\begin{aligned} pk &= 600A, \ T_J = 25^{\circ}C, \ t \ p = 10 ms \ sine \ pulse \\ & (16.7\% \ x \ \pi \ x \ I_{T(AV)} < I < \pi \ x \ I_{T(AV)}), \ T_J = T_J \ max. \\ & (I > \pi \ x \ I_{T(AV)}), T_J = T_J \ max. \\ & (16.7\% \ x \ \pi \ x \ I_{T(AV)} < I < \pi \ x \ I_{T(AV)}), \ T_J = T_J \ max. \end{aligned}$		
V _{T(TO)1}	Low level value of threshold voltage	0.98	٧			
V _{T(TO)2}	High level value of threshold voltage	0.88				
r _{t1}	Low level value of on-state slope resistance	0.81	mΩ			
r _{t2}	High level value of on-state slope resistance	1.55		(I > π x I _{T(AV)}	$),T_J = T_J \text{ max.}$	
I _H	Maximum holding current	600	mA	T _J = 25°C, a	anode supply 12V r	esistive load
IL	Typical latching current	1000 (300)				



Switching

	Parameter	INRN230S	Units	Conditions
di/dt	ax. non-repetitive rate of rise	1000	Λ/μο	Gate drive 20V, 20Ω, tr ≤ 1μs
	of turned-on current	1000	A/μs	T _J = T _J max, anode voltage ≤ 80% V _{DRM}
	ical dalay tima	4.0		Gate current 1A, dig/dt = 1A/µs
td	ical delay time	1.0	μs	Vd = 0.67% VDRM, TJ = 25°C
Ta	pical turn-off time 100 us		$I_{TM} = 600A$, $T_J = T_J max$, $di/dt = 20A/\mu s$, $V_R = 50V$	
Tq	pical turn-off time	100	μs	$dv/dt = 20V/\mu s$, Gate 0V 100Ω, $t_p = 500\mu s$

Blocking

	Parameter	INRN230S	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	400	V/µs	TJ = TJ max linear to 80% rated VDRM
I _{DRM}	Max. peak reverse and off-state leakage current	15	mA	TJ = TJ max, rated VDRM/VRRM applied

Triggering

	Parameter	INR	N230S	Units	Conditions		
M	Maximum peak gate power	1	10.0	W	TJ = TJ max, t	TJ = TJ max, tp 5ms	
P _{G(AV)}	Maximum average gate power		2.0	VV	TJ = TJ max, f = 50Hz, d% = 50		
I _{GM}	Max. peak positive gate current		3.0	А	TJ = TJ max, tp 5ms		
+V _{GM}	Maximum peak positive gate voltage		20	V	TJ = TJ max, tp 5ms		
-VGM	Maximum peak negative gate voltage		5.0	mA			
I _{GT}	DC gate current required	180 90 40	150	mA	$T_{J} = -40^{\circ}C$ $T_{J} = 25^{\circ}C$ $T_{J} = 125^{\circ}C$	Max. required gate trigger, current /voltage are the lowest valuewhich will trigger all units 12V anode-to-cathode applied	
V_{GT}	DC gate voltage required to trigger	2.9 1.8 1.2	3.0	V	$T_J = -40$ °C $T_J = 25$ °C $T_J = 125$ °C	Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V anode-to-cathode applied	
I _{GD}	DC gate current not to trigger		10	mA			
V_{GD}	DC gate voltage not to trigger	(0.25	٧			

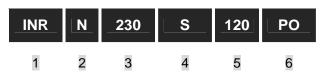


Thermal and Mechanical Specifications

	Parameter	INRN230S	Units	Conditions
T _J	Max. junction operating temperature range	-40 to 125	°C	Junction to case
T _{Stg}	Max. storage temperature range	-40 to 150	°C	
R _{thJC}	Max. thermal resistance, junction to case	0.10	K/W	DC operation
R thSC	Max. thermal resistance, case to heatsink	0.04	N/VV	Mounting surface, smooth, flat and greased
Т	Max. allowed mounting torque +0 -20%	31	Nm	Not lubricated threads
		275	lbf.in	
		24.5	Nm	Lubricated threads
		210	lbf.in	
wt	Approximate weight	280(2512)	g (oz)	
	Case style	TO - 209AB (TO-93)		See Outline Table

Ordering Information Table





INR = Company

= Thyristor

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3 Current rating: Code = IF(AV

S = Stud Normal Polarity (Cathode to Stud) 4 5

P = Stud base 3/4"-16UNF2A threads

Voltage code: Code x 10 = VRRM (See Voltage Ratings table)

0 = Eyelet terminals (Gate and Auxiliary Cathode Leads)

1 = Fast - on terminals (Gate and Auxiliary Cathode Leads)



Outline

